2SB0968 (2SB968)

Silicon PNP epitaxial planar type

For low-frequency output amplification Complementary to 2SD1295

■ Features

- Possible to solder radiation fin directly to printed circuit board
- High collector-emitter voltage (Base open) V_{CEO}
- Large collector power dissipation P_C

■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	-50	V	
Collector-emitter voltage (Base open)	V _{CEO}	-40	V	
Emitter-base voltage (Collector open)	V_{EBO}	-5	V	
Collector current	I_{C}	-1.5	A	
Peak collector current	I_{CP}	-3	A	
Collector power dissipation ($T_C = 25^{\circ}C$)	P _C	10	W	
Junction temperature	Tj	150	°CO	
Storage temperature	T _{stg}	-55 to +150	°C	

■ Package

- Code
 - U-G2
- Pin Name
 - 1: Base
 - 2: Collector
 - 3: Emitter

■ Electrical Characteristics T_a = 25°C ± 3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -1 \text{ mA}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-40			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			-1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = -10 \text{ V}, I_{B} = 0$			-100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$			-10	μΑ
Forward current transfer ratio	h _{FE1} *	$V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ A}$	80		220	_
	h _{FE2}	$V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ mA}$	10			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -1.5 \text{ A}, I_B = -0.15 \text{ A}$			-1	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = -2 \text{ A}, I_B = -0.2 \text{ A}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -5 \text{ V}, I_{C} = -0.5 \text{ A}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		45		pF
(Common base, input open circuited)						

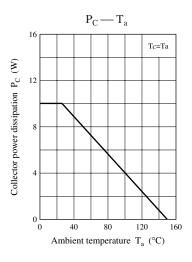
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

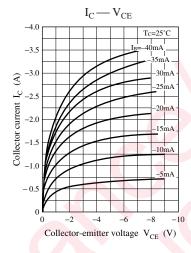
2. *: Rank classification

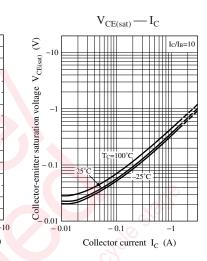
Rank	Q	R		
$h_{\rm FE1}$	80 to 160	120 to 220		

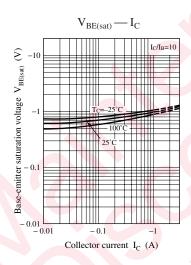
Note) The part number in the parenthesis shows conventional part number.

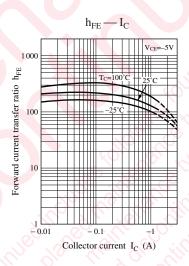
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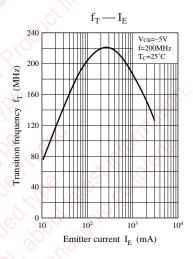


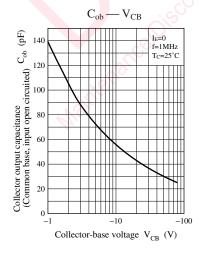


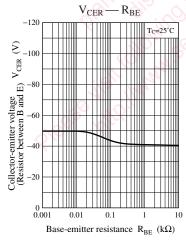


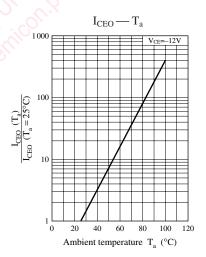




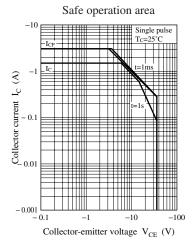




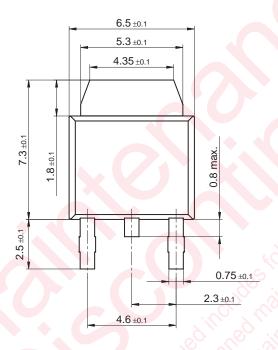


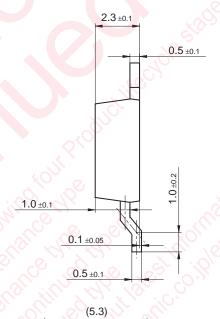


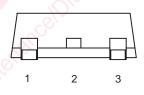
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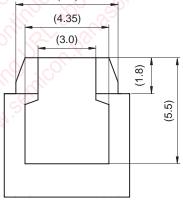


U-G2 Unit: mm









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